

AP9990GMT-HF-VB Datasheet

N-Channel 60 V (D-S) MOSFET

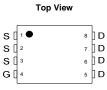
PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a		
60	0.006 at V _{GS} = 10 V	80		
	0.007 at V _{GS} = 4.5 V	65		

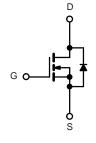
FEATURES

- 175 °C Junction Temperature
- Trench Power MOSFET
- Material categorization:









N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C	= 25 °C, unless othe	rwise noted)			
Parameter		Symbol	Limit	Unit	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current $(T_1 = 175 \text{ °C})^b$	T _C = 25 °C	1-	80		
Continuous Drain Current $(T_j = 175 \text{ °C})^2$	T _C = 100 °C	I _D	65 ^a		
Pulsed Drain Current		I _{DM}	100	А	
Continuous Source Current (Diode Conduction)		۱ _S	70 ^a		
Avalanche Current		I _{AS}	50	7	
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Maximum Power Dissipation	T _C = 25 °C	P	136	W	
	T _A = 25 °C	P _D	3 ^b , 8.3 ^{b, c}	vv	
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marine lugation to Archienta	$t \le 10 \text{ sec}$	R _{thJA}	15	18	°C/W
Maximum Junction-to-Ambient ^a	Steady State		40	50	
Maximum Junction-to-Case		R _{thJC}	0.85	1.1	

Notes:

a. Package limited.

c. t \leq 10 s.

b. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static	_			_			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60			v	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.5		4		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			50		
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 \text{ °C}$			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	60			А	
		V _{GS} = 10 V, I _D = 20 A		0.006		Ω	
	D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.010			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C		0.015			
		V _{GS} = 4.5 V, I _D = 15 A		0.007			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic	•	•		•			
Input Capacitance	C _{iss}			2650		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		470			
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Qg			47	70	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$		10			
Gate-Drain Charge ^c	Q _{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{L}} = 0.6 \Omega$ $\text{I}_{\text{D}} \cong 50 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 2.5 \Omega$		15	25	ns .	
Turn-Off Delay Time ^c	t _{d(off)}			35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				60	А	
Diode Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/µs		45	100	ns	

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Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. Independent of operating temperature.

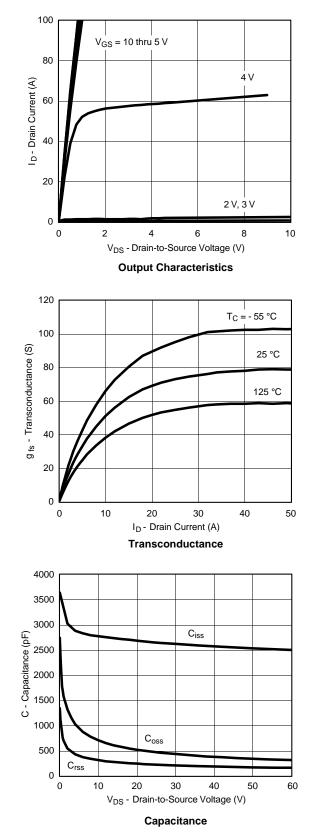
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

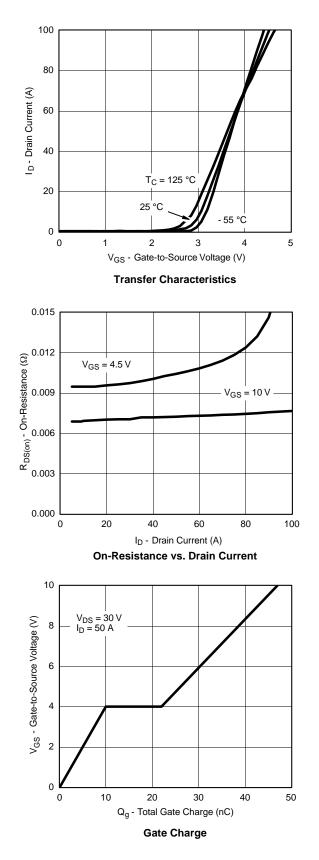
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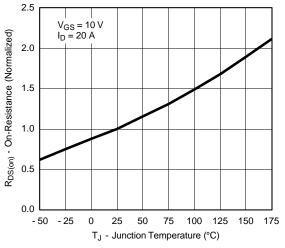
TYPICAL CHARACTERISTICS (25 °C unless noted)



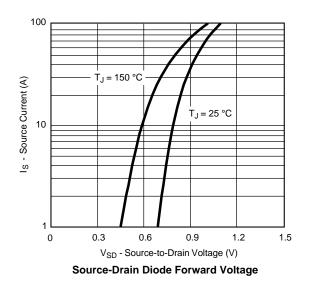




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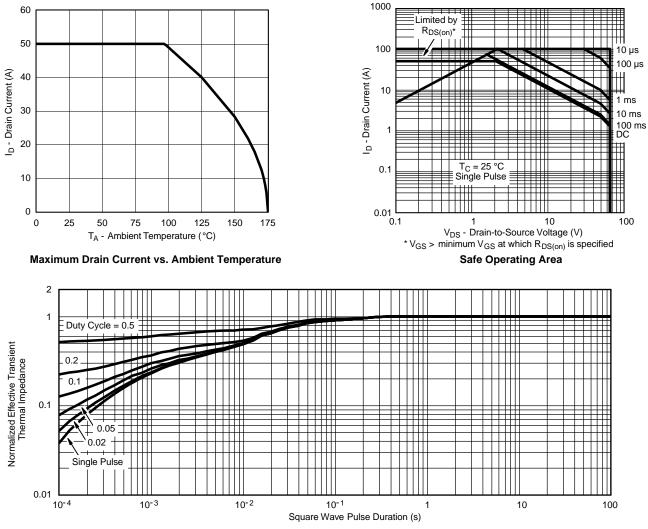
On-Resistance vs. Junction Temperature



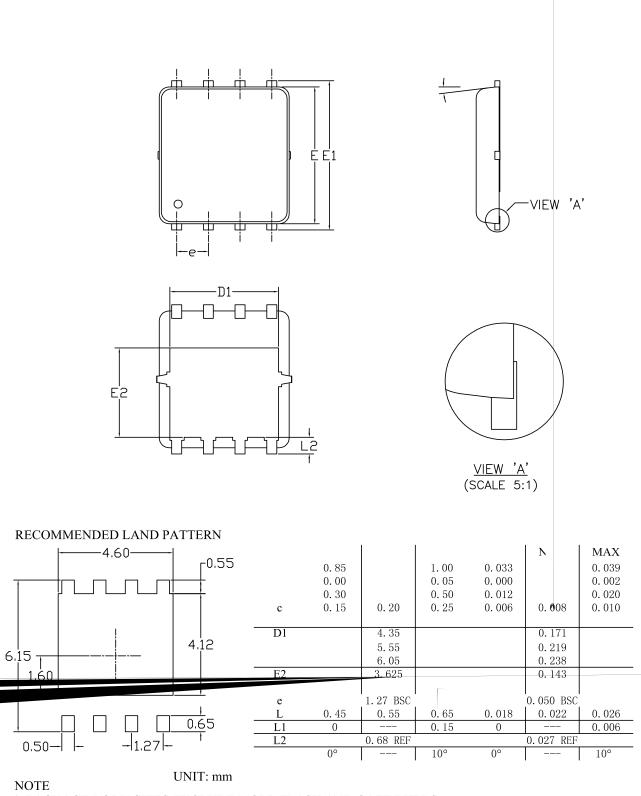
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THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



 PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
CONTROLLING DIMENSION IS MILLIMETER.

CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.



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